USB 2.0-Capable Ultra-Low THD DPDT Switch

The NL3S588 is a single supply, bidirectional, double-pole/ double-throw (DPDT) switch suitable for both hi-fidelity audio and high-speed data applications.

The NL3S588 features ultra-low distortion, high OFF–Isolation analog switches that can pass analog signals that are positive and negative with respect to ground. It is targeted at consumer and professional DC–coupled GND–referenced audio switching applications such as computer sound cards and home theater products.

The NL3S588 may also be used in high-speed differential data routing applications. Both channels are USB 2.0-compliant.

Features

- DPDT Switch
- 3.3 V Single Supply Operation
- Available in 1.4 mm x 1.8 mm UQFN10
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Audio Capabilities

- 2 V_{RMS} Signal Switching
- -116 dB THD+N into 20 k Ω Load at 2 V_{RMS}
- -112 dB THD+N into 32Ω Load at 0.707 V_{RMS}
- Signal to Noise Ratio: > 125 dBV
- ± 0.004 dB Insertion Loss at 1 kHz, 20 k Ω Load
- ±0.0008 dB Gain Variation 20 Hz to 20 kHz
- 112 dB Signal Muting into 20 k Ω Load
- 131 dB PSRR 20 Hz to 20 kHz

High-Speed Data Capabilities

- Input Signal Range: 0 V to V_{DD}
- C_{ON}: 8.9 pF (Typ)
- Data Rate: USB 2.0-Compliant up to 480 Mbps
- Bandwidth: 580 MHz

Applications

- Hi-Fi Audio Switching
- USB 2.0 High–Speed Data Switching
- USB 3.x Type C Switching



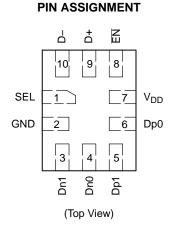
ON Semiconductor®

www.onsemi.com



= Pb-Free Device

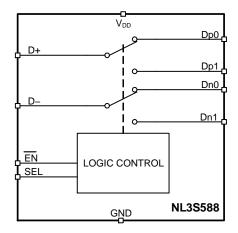
(Note: Microdot may be in either location)



ORDERING INFORMATION

Device	Package	Shipping [†]		
NL3S588MUTBG	UQFN10 (Pb-Free)	3000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.





FUNCTION TABLE

INP	UTS	
EN	SEL	Operating Mode
0	0	Dp0 connected to D+ / Dn0 connected to D-
0	1	Dp1 connected to D+ / Dn1 connected to D-
1	Х	Shutdown (I/Os Disconnected)

NOTE: $\overline{\text{EN}}$ Logic "0" \leq 0.5 V, Logic "1" \geq 1.4 V or float. SEL Logic "0" \leq 0.5V, Logic "1" \geq 1.4 V. X = Don't Care

PIN DESCRIPTIONS

PIN NAME	PIN	DESCRIPTION
SEL	1	Channel Select
GND	2	Ground
Dn1	3	Normally-Open I/O
Dp1	5	
Dn0	4	Normally–Closed I/O
Dp0	6	
V _{DD}	7	System power supply pin (+3 V to +3.6 V)
EN	8	Signal mute control pin
D+	9	Common I/O
D-	10	

MAXIMUM RATINGS

Symbol	Rating		Value	Unit
V _{DD}	Positive 3 V DC Supply Voltage		-0.5 to +4.1	V
V _{IS}	Analog Input/Output Voltage (D+, D-, Dpx, Dnx)		–3.1 to V _{DD} + 0.5	V
V _{IN}	Digital Input Voltage (EN, SEL)		–0.5 to V _{DD} + 0.5	V
I _{IO}	Switch Continuous Current (D+, D–, Dpx, Dnx)		±300	mA
I _{IO_PK}	Switch Peak Current (D+, D–, Dpx, Dnx) (Pulsed 1 ms, 10% Duty Cycle, Max).		±500	mA
PD	Power Dissipation in Still Air		800	mW
Ts	Storage Temperature		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 seconds		260	°C
TJ	Junction Bias Under Bias		150	°C
θ_{JA}	Thermal Resistance		80	°C/W
Τs	Storage Temperature		-65 to +150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating C	xygen Index: 30% – 35%	UL94–V0 (0.125 in)	°C
ESD	ESD Protection	Human Body Model Machine Model	3000 200	V
۱ _L	Latch-up Current, Above V _{CC} and below GND at	125°C (Note 1)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{DD}	Positive DC Supply Voltage	3.0	3.6	V
V _S	Switch Input / Output Voltage (D+, D–, Dpx, Dnx)	-2.9	V _{DD}	V
V _{IN}	Digital Select Input Voltage (EN, SEL)	GND	V _{DD}	V
T _A	Operating Temperature Range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): $V_{DD} = +3.0 \text{ V}$ to +3.6 V, GND = 0 V, $V_S = 2 \text{ V}_{RMS}$, $R_{LOAD} = 20 \text{ k}\Omega$, f = 1 kHz, $V_{SELH} = V_{ENH} = 1.4 \text{ V}$, $V_{SELL} = V_{ENL} = 0.5 \text{ V}$, (Note 2), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
ANALOG SWITCH CHARACTERISTICS							
Analog Signal Range, V _{ANALOG}		3.3	Full	-	2	-	V _{RMS}
ON-Resistance, r _{ON}	N-Resistance, r_{ON} I_{D+} or $I_{D-} = 80$ mA, V_{Dpx} or $V_{Dnx} = -2.828$ V to +2.828 V (See Figure 5)	3.3	25	-	2.1	-	Ω
			Full	-	2.5	-	
r _{ON} Matching Between	I_{D+} or I_{D-} = 80mA, V_{Dpx} or V_{Dnx} =	3.3	25	-	0.046	-	Ω
$ Channels, \Delta r_{ON} \qquad \qquad \ \ Voltage at max r_{ON} over -2.828 V \\ to +2.828 V (Note 7) $		Full	-	0.23	-		
r _{ON} Flatness, r _{FLAT(ON)}	AT(ON) I_{D+} or $I_{D-} = 80$ mA, V_{Dpx} or $V_{Dnx} = -2.828$ V, 0V, +2.828 V (Note 5)	3.3	25	-	0.047	0.05	Ω
	-2.828 V, UV, +2.828 V (Note 5)		Full	-	0.092	-	

2. V_{IN} = input voltage to perform proper function.

3. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

 Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

6. Limits established by characterization and are not production tested.

7. r_{ON} matching between channels is calculated by subtracting the channel with the highest max r_{ON} value from the channel with lowest max r_{ON} value.

8. Crosstalk is inversely proportional to source impedance.

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): V _{DD} = +3.0 V to +3.6 V, GND = 0 V, V _S = 2 V _{RMS} , R _{LOAD} =
20 k Ω , f = 1 kHz, V _{SELH} = V _{ENH} = 1.4 V, V _{SELL} = V _{ENL} = 0.5 V, (Note 2), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
ANALOG SWITCH CHARAC	TERISTICS						
D+, D–, Dpx, Dnx Pull– down Resistance	V_{Dpx} or $V_{Dnx} = -2.83$ V, 2.83 V, V_{D+} or $V_{D-} = -2.83$ V, 2.83 V, $V_{EN} = 3.6$ V, measure current,	3.6	25 Full	225	300 345	375	kΩ
	calculate resistance.		1 UII		040		
DYNAMIC CHARACTERIST			-				
THD+N	V_S = 2 $V_{RMS},$ f = 1 kHz, A–weighted filter, R_{LOAD} = 20 $k\Omega$	3.3	25	-	< -116	-	dB
	$V_S = 1.9 V_{RMS}$, f = 1 kHz, A–weight- ed filter, R _{LOAD} = 20 k Ω		25	-	< -116	-	
	V_S = 1.8 V_{RMS} , f = 1 kHz, A-weight- ed filter, R _{LOAD} = 20 k Ω		25	-	< -116	-	
	V_S = 0.707 V_{RMS} , f = 1 kHz, A–weighted filter, R _{LOAD} = 32 Ω		25	-	< -112	-	
SNR	f = 20 Hz to 20 kHz, A–weighted filter, inputs grounded, R_{LOAD} = 20 kΩ or 32 Ω	3.3	25	-	> 125	-	dBV
Insertion Loss, G _{ON}	f = 1 kHz, R_{LOAD} = 20 k Ω	3.3	25	-	±0.004	-	dB
Gain vs Frequency, G _f	f = 20 Hz to 20 kHz, R_{LOAD} = 20 kΩ, reference to G_{ON} at 1 kHz	3.3	25	-	±0.0008	-	dB
Stereo Channel Imbalance Dp0 and Dn0, Dp1 and Dn1	f = 20 Hz to 20 kHz, R_{LOAD} = 20 k Ω	3.3	25	-	±0.0001	-	dB
OFF–Isolation (Disabling)	f = 20 Hz to 22 kHz, D+ = D- = 2 V _{RMS} , R _{LOAD} = 20 kΩ, = 3.3 V, SEL = "X"	3.3	25	-	112	-	dB
	f = 20 Hz to 22 kHz, V_{D+} or V_{D-} = 0.7 V_{RMS} , R_{LOAD} = 32 Ω		25	-	129	-	
Crosstalk (Channel-to- Channel)	$ \begin{array}{l} R_{L} = 20 \; k\Omega, f = 20 \; Hz \; to \; 20 \; kHz, \\ V_{S} = 2 \; V_{RMS}, signal \; source \; imped- \\ ance = 20 \; \Omega, (Note \; 8) \end{array} $	3.3	25	_	102	-	dB
	R_L = 32 Ω, f = 20 Hz to 20 kHz, V _S = 0.7 V _{RMS} , signal source imped- ance = 20 Ω, (Note 8)		25	_	129	-	
PSRR	$f = 1 \text{ kHz}, V_S = 100 \text{ mV}_{RMS}$, inputs grounded	3.3	25	-	131	-	dB
	$f = 20 \text{ kHz}, V_S = 100 \text{ mV}_{RMS}$, inputs grounded		25	-	133	-	
Bandwidth, -3 dB	$R_{LOAD} = 50 \ \Omega$	3.3	25	-	580	- 1	MHz
ON to Disable Time, T _{TRANS-OM}		3.3	25	-	250	-	ns
Disable to ON Time, T _{TRANS-MO}	V _{IS} = 1.5 V	3.3	25	-	1680	-	μS
Turn–ON Time, t _{ON}	V_{Dpx} or V_{Dnx} = 1.5 V, V_{EN} = 0 V, R _L = 32 Ω (See Figure 2)	3.3	25	-	14	-	μS
Turn-OFF Time, t _{OFF}	V_{Dpx} or V_{Dnx} = 1.5 V, V_{EN} = 0 V, R _L = 32 Ω (See Figure 2)	3.3	25	-	95	-	ns

V_{IN} = input voltage to perform proper function.
The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by charac-

terization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

 Limits established by characterization and are not production tested.
r_{ON} matching between channels is calculated by subtracting the channel with the highest max r_{ON} value from the channel with lowest max r_{ON} value. 8. Crosstalk is inversely proportional to source impedance.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
DYNAMIC CHARACTERIST	ICS						
Break–Before–Make Time Delay, t _D	V_{Dpx} or V_{Dnx} = 1.5V, V_{EN} = 0V, R _L = 32 Ω (See Figure 3)	3.6	25	-	10	-	μs
OFF-Isolation	$ \begin{array}{l} R_{L} = 50 \; \Omega, f = 1 \; MHz, V_{D+} \\ or \; V_{D-} = 1 \; V_{RMS} \; (See Figure 4) \end{array} $	3.3	25	-	70	-	dB
Crosstalk (Channel-to-Channel)	$R_L = 50 \Omega$, f = 1 MHz, V_{D+} or $V_{D-} = 1 V_{RMS}$ (See Figure 4)	3.3	25	-	89	-	dB
Dpx, Dnx OFF Capaci- tance, C _{OFF}	$ f = 1 \text{ MHz}, V_{Dpx} \text{ or } V_{Dnx} = V_{D+} $ or $V_{D-} = 0 \text{ V}$ (See Figure 7)	3.3	25	-	2.7	-	pF
D+, D– ON Capacitance, C _{COM(ON)}	$f = 1 MHz, V_{Dpx} \text{ or } V_{Dnx} = V_{COM} = 0 V (See Figure 7)$	3.3	25	-	8.9	-	pF
Differential Insertion	f = 10 MHz	3.3	25	-	-0.22	-	dB
Loss, D _{IL}	f = 800 MHz	3.3	25	-	-3.3	-	
Differential OFF-	f = 10 MHz	3.3	25	-	-44	-	dB
Isolation, D _{ISO}	f = 800 MHz	3.3	25	-	-16	-	
Differential	f = 10 MHz	3.3	25	-	-44	-	dB
Crosstalk, D _{CTK}	f = 800 MHz	3.3	25	-	–16	-	

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): V _{DD} = +3.0 V to +3.6 V, GND = 0 V, V _S = 2 V _{RMS} , R _{LOAD} =
20 k Ω , f = 1 kHz, V _{SELH} = V _{ENH} = 1.4 V, V _{SELL} = V _{ENL} = 0.5 V, (Note 2), Unless otherwise specified.

POWER SUPPLY CHARACTERISTICS

Power Supply Range, V _{DD}		3.3	Full	3	-	3.6	V
Positive Supply	$V_{EN} = 0 V$, $V_{SEL} = 0 V$ or V_{DD}	3.6	25	-	54	65	μΑ
Current, I+			Full	-	59	-	
	$V_{EN} = V_{DD}, V_{SEL} = 0 V \text{ or } V_{DD}$	3.6	25	-	14	40	μA
			Full	-	15	-	
	V _{EN} = 0 V, V _{SEL} = 1.8 V	3.6	25	-	55	65	μΑ
			Full	-	58	-	

2. V_{IN} = input voltage to perform proper function.

 The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

6. Limits established by characterization and are not production tested.

7. ron matching between channels is calculated by subtracting the channel with the highest max ron value from the channel with lowest max r_{ON} value.

8. Crosstalk is inversely proportional to source impedance.

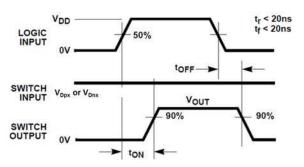
DC ELECTRICAL CHARACTERISTICS – **Digital Section** (Voltages referenced to GND): V_{DD} = +3.0 V to +3.6 V, GND = 0 V, V_S = 2 V_{RMS} , R_{LOAD} = 20 k Ω , f = 1 kHz, V_{SELH} = V_{ENH} = 1.4 V, V_{SELL} = V_{ENL} = 0.5 V, (Note 9), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 10, 11)	Тур	Max (Notes 10, 11)	Units
DIGITAL INPUT CHARACT	ERISTICS						
Input Voltage Low, V _{SELL} , V _{ENL}		3.3	Full	-	-	0.5	V
Input Voltage High, V _{SELH} , V _{ENH}		3.3	Full	1.4	-	-	V
Input Current, I _{SELH} , I _{SELL}	V_{EN} = 0 V, V_{SEL} = 0 V or V_{DD}	3.6	Full	-0.5	0.01	0.5	μΑ
Input Current, I _{ENL}	$V_{SEL} = V_{DD}, V_{EN} = 0 V$	3.6	Full	-1.3	-0.7	0.3	μΑ
Input Current, I _{ENH}	$V_{SEL} = 0 V, V_{EN} = V_{DD}$	3.6	Full	-0.5	0.01	0.5	μΑ

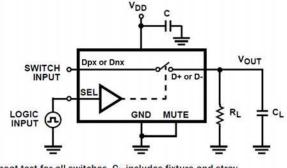
9. V_{IN} = input voltage to perform proper function.

10. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet. 11. Parameters with MIN and/or MAX limits are 100% tested at +25^[2]C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

TEST CIRCUITS AND WAVEFORMS



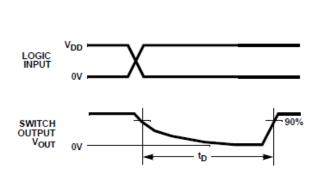
Logic input waveform is inverted for switches that have the opposite logic sense.

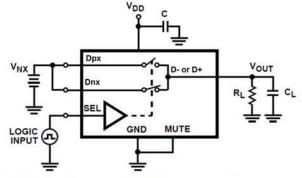


Repeat test for all switches. C_L includes fixture and stray capacitance. $V_{OUT} = V_{(Dpx \text{ or } Dnx)} \frac{R_L}{R_L + rON}$

Test Circuit







Repeat test for all switches. CL includes fixture and stray capacitance.

Measurement Points

Test Circuit

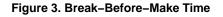
Dpx or Dnx

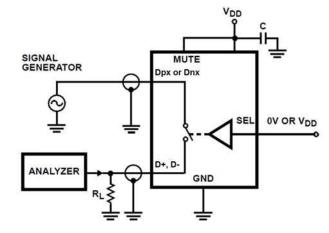
VDD

SEI

GND MUTE

OV OR VDD





Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

Figure 4. Off–Isolation Test Circuit

Repeat test for all switches.

ron = V1/80mA

80mA (4

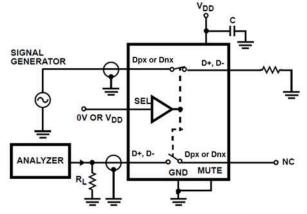
V

VNX



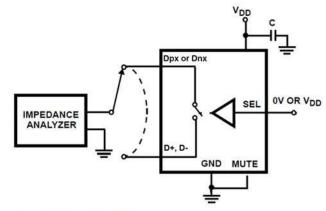
D+, D-

TEST CIRCUITS AND WAVEFORMS



Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

Figure 6. Crosstalk Test Circuit



Repeat test for all switches.

Figure 7. Capacitance Test Circuit

TYPICAL PERFORMANCE CURVES:

 T_A = +25°C, Unless Otherwise Specified

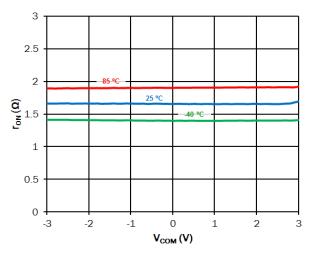
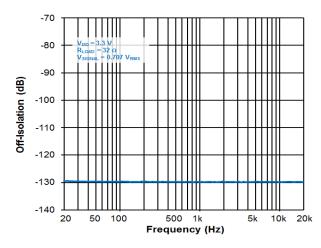
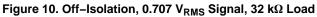


Figure 8. On-Resistance vs. Switch Voltage





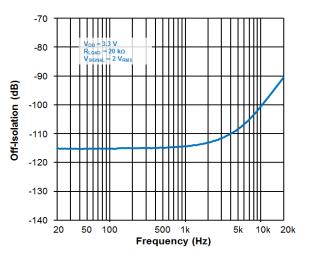
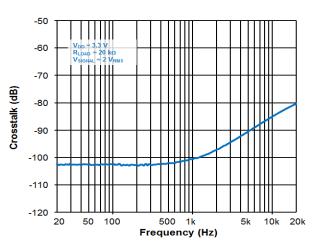


Figure 9. Off–Isolation, 2 V_{RMS} Signal, 20 k Ω Load





TYPICAL PERFORMANCE CURVES:

 $T_A = +25^{\circ}C$, Unless Otherwise Specified

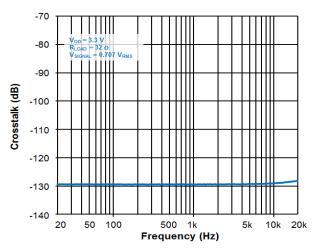
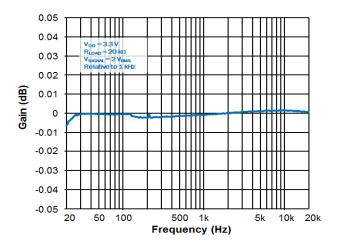
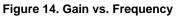


Figure 12. Channel-to-Channel Crosstalk





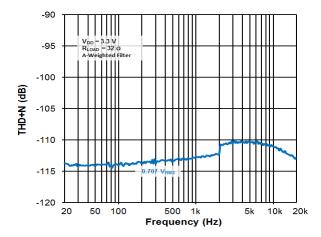


Figure 16. THD+N vs. Signal Levels vs. Frequency

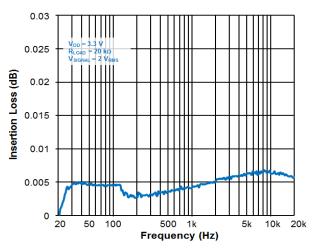


Figure 13. Insertion Loss vs. Frequency

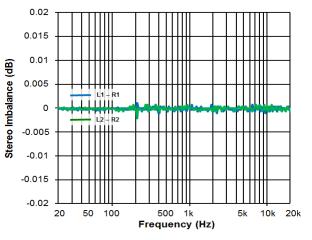


Figure 15. Stereo Imbalance vs. Frequency

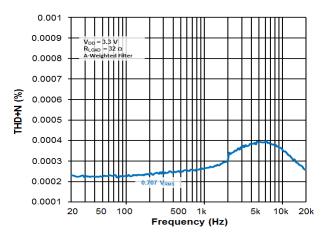


Figure 17. THD+N vs. Signal Levels vs. Frequency

TYPICAL PERFORMANCE CURVES:

 T_A = +25°C, Unless Otherwise Specified

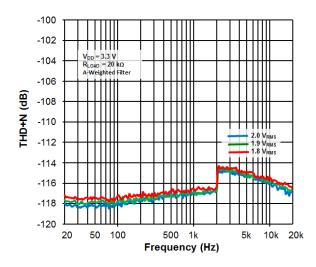


Figure 18. THD+N vs. Signal Levels vs. Frequency

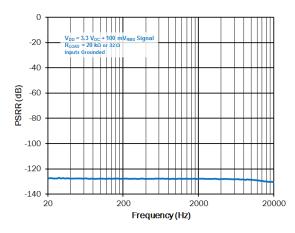


Figure 20. PSRR vs. Frequency

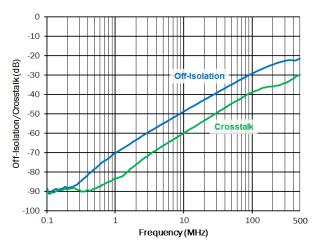


Figure 22. Crosstalk and Off–Isolation

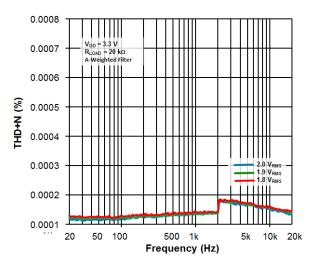


Figure 19. THD+N vs. Signal Levels vs. Frequency

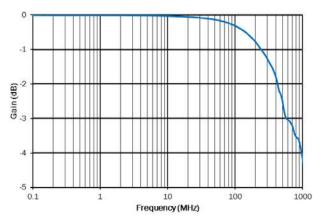


Figure 21. Frequency Response

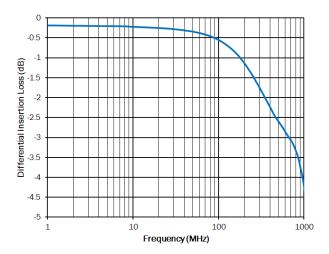


Figure 23. Differential Crosstalk

TYPICAL PERFORMANCE CURVES:

 T_A = +25°C, Unless Otherwise Specified

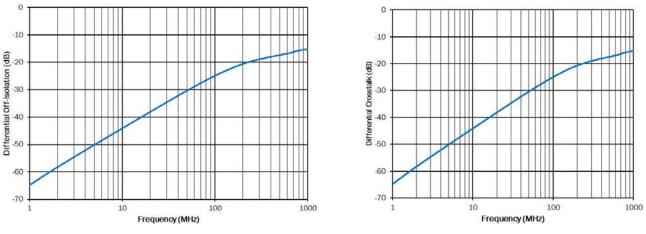
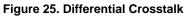


Figure 24. Differential Off–Isolation



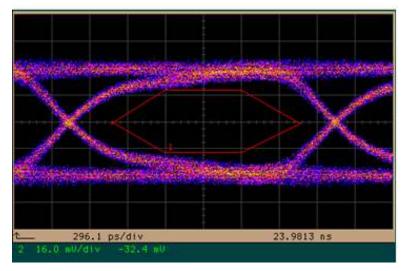
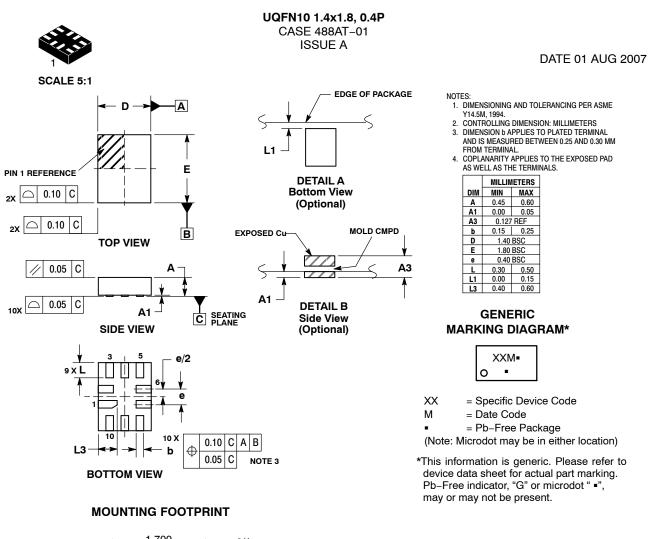


Figure 26. USB 2.0 High–Speed Eye Diagram





$0.663 \xrightarrow{1.700}{0.0669} \xrightarrow{9 \times \\ 0.563 \\ 0.0221}$	
0.400 0.0157 PITCH	
\rightarrow \sim 0.0089 SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$	<u>,</u>)

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DESCRIPTION:	10 PIN UQFN, 1.4 X 1.8, 0.4P		PAGE 1 OF 1	
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